1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a leadless ultra small DSN1006-2 (SOD993) Surface-Mounted Device (SMD) package.

2. Features and benefits

Average forward current: I_{F(AV)} ≤ 1 A

Reverse voltage: V_R ≤ 30 V

Low forward voltage, typical: V_F = 495 mV
 Low reverse current, typical: I_R = 12 μA

Package height typ. 270 μm

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Low power consumption applications
- Ultra high-speed switching
- · LED backlight for mobile application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current	T _{sp} ≤ 135 °C; δ = 1	-	-	1.4	Α
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 140 °C; square wave	-	-	1	A
V _R	reverse voltage	T _j = 25 °C	-	-	30	V
V _F	forward voltage	I_F = 1 A; t_p ≤ 300 μs; δ ≤ 0.02 ; T_j = 25 °C	-	495	565	mV
I _R	reverse current	$V_R = 30 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ;$ $T_j = 25 \text{ °C}$	-	12	45	μA
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$	-	3.2	-	ns





5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		1 - 2
2	A	anode	1 2	sym001
			Transparent top view DSN1006-2 (SOD993)	

^[1] The marking bar indicates the cathode.

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG3010ESB	DSN1006-2	DSN1006-2, leadless ultra small package; 2 terminals; body 1.0 x 0.6 x 0.27 mm	SOD993			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG3010ESB	3E

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30 V, 1 A low VF MEGA Schottky barrier rectifier

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _R	reverse voltage	T _j = 25 °C		-	30	V
I _F	forward current	T _{sp} ≤ 135 °C; δ = 1		-	1.4	Α
I _{F(AV)}	average forward current	$\bar{\delta}$ = 0.5 ; f = 20 kHz; $T_{amb} \le 105$ °C; square wave	[1]	-	1	A
		δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 140 °C; square wave		-	1	A
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ ms}; \delta \le 0.25$		-	4	Α
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	10	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	0.525	W
			[3]	-	1	W
			[1]	-	1.78	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm² each.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient			[1][2]	-	-	240	K/W
			[1][3]	-	-	125	K/W
	ambient		[1][4]	-	-	70	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[5]	-	-	15	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm² each.
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of anode tab.

PMEG3010ESB

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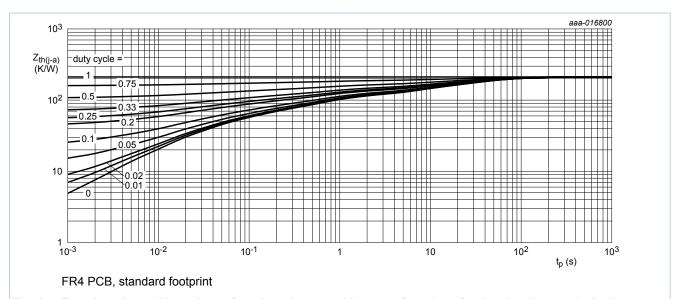


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

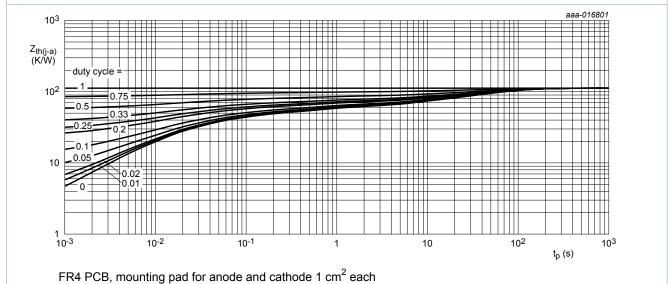
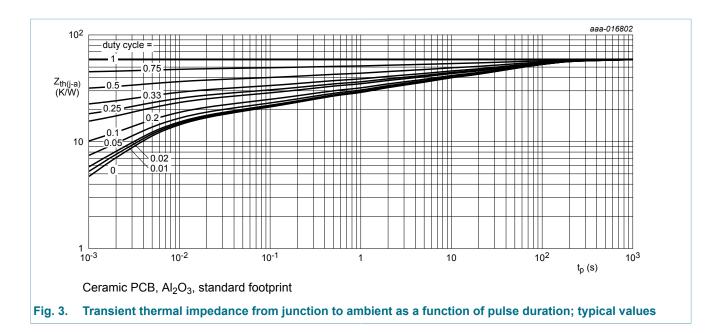


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, 1 A low VF MEGA Schottky barrier rectifier



30 V, 1 A low VF MEGA Schottky barrier rectifier

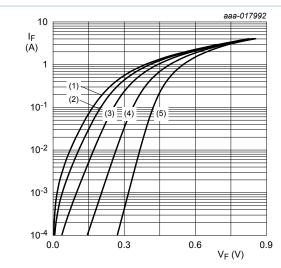
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)R}	reverse breakdown voltage	I_R = 1 mA; t_p = 300 μ s; δ = 0.02 ; T_j = 25 °C	30	-	-	V
V _F for	forward voltage	I_F = 1 mA; $t_p \le 300 \text{ µs}$; $\delta \le 0.02 \text{ ;}$ T_j = 25 °C	-	205	-	mV
		I_F = 10 mA; t_p ≤ 300 μs; δ ≤ 0.02 ; T_j = 25 °C	-	265	-	mV
		I_F = 100 mA; t_p ≤ 300 μs; δ ≤ 0.02 ; T_j = 25 °C	-	340	375	mV
		I_F = 200 mA; t_p ≤ 300 μs; δ ≤ 0.02 ; T_j = 25 °C	-	370	-	mV
		I_F = 500 mA; t_p ≤ 300 μs; δ ≤ 0.02 ; T_j = 25 °C	-	425	475	mV
		I_F = 700 mA; $t_p \le 300 \ \mu s$; $\delta \le 0.02 \ ;$ T_j = 25 °C	-	455	-	mV
		I_F = 1 A; t_p ≤ 300 μs; \bar{o} ≤ 0.02 ; T_j = 25 °C	-	495	565	mV
R	reverse current	$V_R = 5 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ; T_j = 25 \text{ °C}$	-	0.9	-	μΑ
		$V_R = 10 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ;$ $T_j = 25 \text{ °C}$	-	1.6	5	μA
		$V_R = 20 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ;$ $T_j = 25 \text{ °C}$	-	3.5	12	μΑ
		$V_R = 30 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ;$ $T_j = 25 \text{ °C}$	-	12	45	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	86	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	32	-	pF
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_i = 25 ^{\circ}\text{C}$	-	3.2	-	ns

6 / 15

30 V, 1 A low VF MEGA Schottky barrier rectifier



pulsed condition

(1)
$$T_i = 150 \, ^{\circ}C$$

(2)
$$T_i = 125 \, ^{\circ}C$$

(3)
$$T_i = 85 \, ^{\circ}C$$

(4)
$$T_i = 25 \, ^{\circ}C$$

(5)
$$T_i = -40 \, ^{\circ}\text{C}$$

Fig. 4. Forward current as a function of forward voltage; typical values

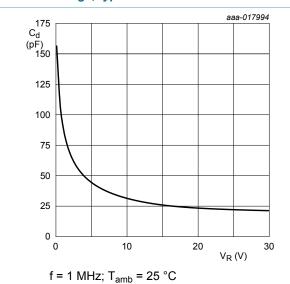
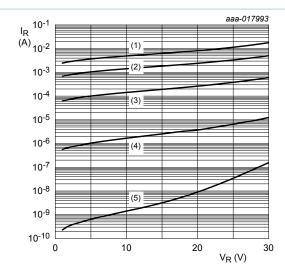


Fig. 6. Diode capacitance as a function of reverse voltage; typical values



pulsed condition

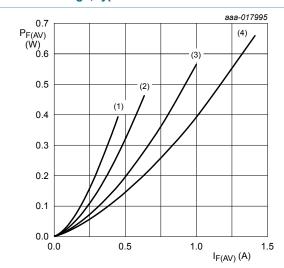
(1)
$$T_i = 150 \, ^{\circ}\text{C}$$

(2)
$$T_i = 125 \, ^{\circ}C$$

(3)
$$T_j = 85 \, ^{\circ}C$$

(4)
$$T_i = 25 \, ^{\circ}C$$

Fig. 5. Reverse current as a function of reverse voltage; typical values



$$(1) \delta = 0.1$$

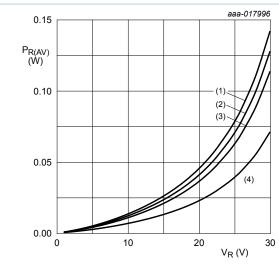
(2)
$$\delta = 0.2$$

$$(3) \delta = 0.5$$

$$(4) \delta = 1$$

ig. 7. Average forward power dissipation as a function of average forward current; typical values

30 V, 1 A low VF MEGA Schottky barrier rectifier



T_i = 125 °C

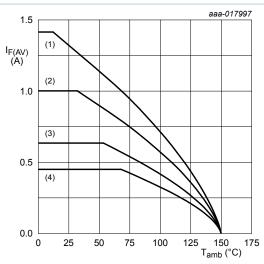
, (1) δ = 1

 $(2) \delta = 0.9$

 $(3) \delta = 0.8$

 $(4) \delta = 0.5$

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

 $T_i = 150 \,{}^{\circ}\text{C}$

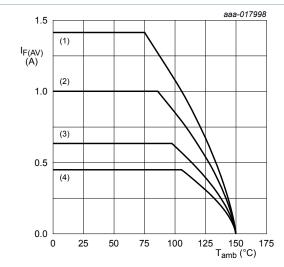
(1) δ = 1; DC

(2) $\delta = 0.5$; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for anode and cathode 1 cm² each

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 $T_j = 150 \,{}^{\circ}\text{C}$

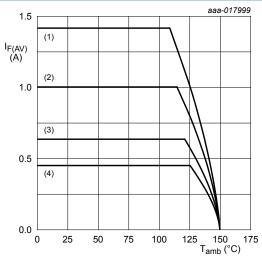
(1) δ = 1; DC

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

 $T_i = 150 \,{}^{\circ}\text{C}$

 $(1) \delta = 1 (DC)$

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

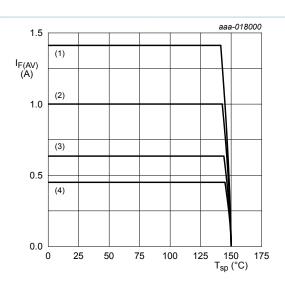
(4) δ = 0.1; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values

PMEG3010ESB

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T_i = 150 °C

(1) $\delta = 1$ (DC)

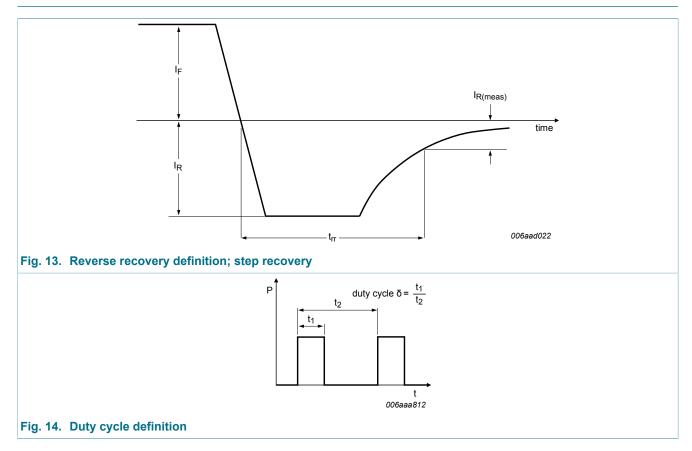
(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

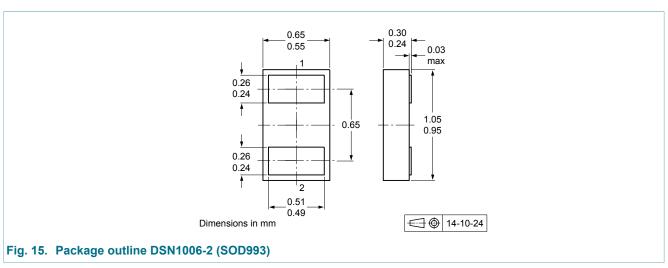
Fig. 12. Average forward current as a function of solder point temperature; typical values

11. Test information



The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

12. Package outline

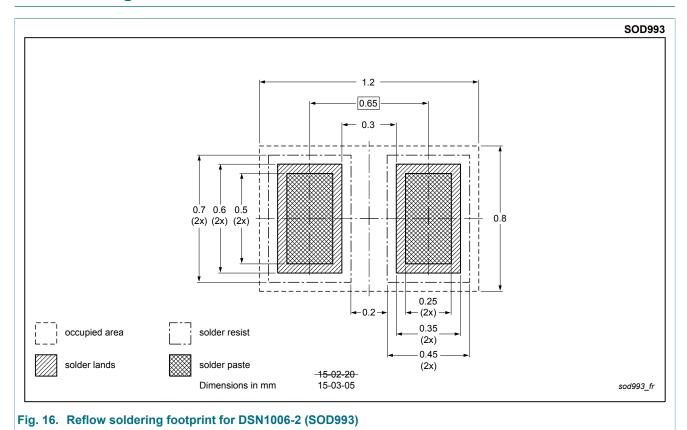


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13. Soldering



14. Mounting

SOD993 is an ultra small Discretes Silicon No-leads (DSN) package allowing maximized utilization of the package area for active silicon. Due to the special product design, NXP investigated the board assembly process parameters. In order to have an optimum soldering quality, NXP advises following the assembly recommendations explained in AN11689.

15. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3010ESB v.3	20160108	Product data sheet	-	PMEG3010ESB v.2
Modification:	Section added: 14.	Mounting		
PMEG3010ESB v.2	20150701	Product data sheet	-	PMEG3010ESB v.1
PMEG3010ESB v.1	20150512	Preliminary data sheet	-	-

12/15

16. Legal information

16.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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17. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	3
10	Characteristics	6
11	Test information	10
12	Package outline	10
13	Soldering	11
14	Mounting	11
15	Revision history	12
16	Legal information	13
16.1	Data sheet status	
16.2	Definitions	13
16.3	Disclaimers	13
16.4	Trademarks	14

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